



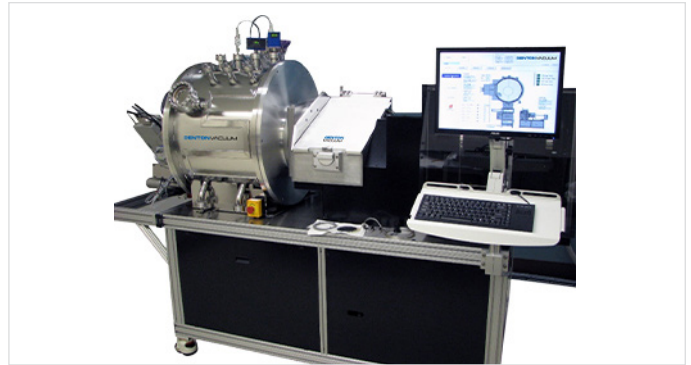
INFINITY ION BEAM ETCH SOLUTION

TECHNICAL SPECIFICATION SHEET

Patented substrate bias option for low damage etching of sensitive structures used in advanced semiconductor processing.

BENEFITS INCLUDE:

- Low plasma damage etch
- High power etch with electrostatic chuck
- Etch rate selectivity for multiple materials by reactive ion etch and chemically assisted etch
- Precise delayering and end point control with SIMS detector



FEATURES		BENEFITS	
Bias substrate	Low plasma damage etch		
Reactive ion beam etch	Material etch rate selectivity		
Chemically assisted ion beam etch	Material etch rate selectivity		
Secondary ion mass spectrometer	Precise delayering and end point control		
Compatible with front-end options	Easily scalable to meet throughput demands		
Automation software	Enhanced process control		
Short MTTR/Long MTBF	High system uptime and ease of maintenance		

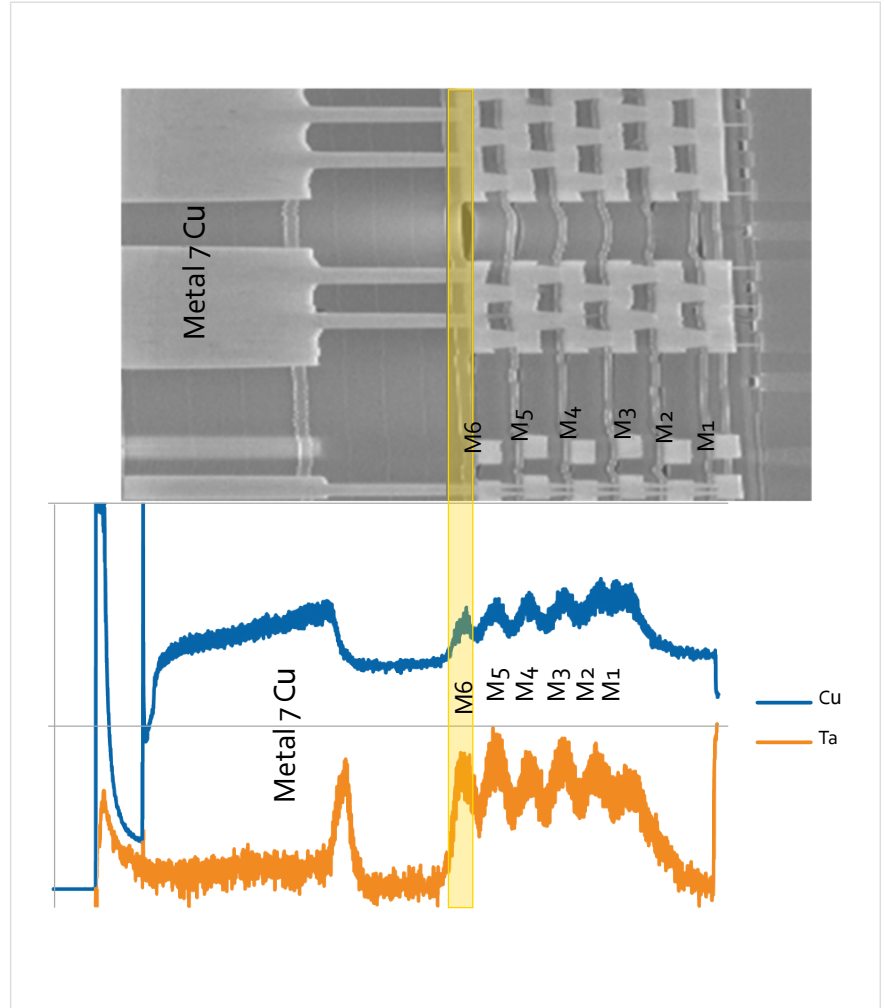
SYSTEM OVERVIEW

Ion beam etching (IBE) uses an energetic, broad beam collimated and highly directional ion source to physically mill material from a substrate mounted on a rotating fixture with adjustable tilt angle. The ion sources used are gridded ion sources of the Kaufman type and are typically neutralized with an independent electron source. Large and small ion sources are available and capable of uniform etching over areas as large as 9 inches in diameter. The highly collimated, directional ion flux allows for anisotropic etching of any material. The ability to modify the angle of the substrate allows the creation of processes that result in tailored sidewall profiles with minimal sputtered redeposition on overlying masks.

The Denton Infinity Ion Beam Etch system is a versatile product addressing several significant markets. This system boasts high performance etching, critical thin film profile milling, glancing angle milling and more. It addresses the needs of customers seeking a flexible, high throughput, cost-effective failure analysis and yield improvement processing. The system is capable of single chip or multiple chip configuration. The system is available in three configurations: standard ion beam etch, reactive ion beam etch and chemically assisted ion beam etch.

APPLICATIONS:

- Semiconductor process yield improvement with end point control
- Compound semiconductor Au etch
- Process control and chip design assessment
- Patterned etch
- FBAR and SAW device trimming for frequency control



SIMS detection of materials for delayering and endpoint.

CONFIGURATION OPTIONS

MODULE	SIMS	Electrostatic Chuck	Bias Chuck
ETCH	Ion Beam	Reactive Ion Beam	Chemically Assisted Ion Beam
FRONT ENDS	Single Wafer Load Lock	Cassette Load Lock	Cluster Tool Front End